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MOS FET

### MTM861270LBF

# **Panasonic**

### MTM861270LBF

### Silicon P-channel MOSFET

#### For Switching

#### ■ Features

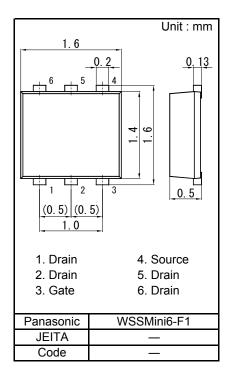
- Low drain-source On-state Resistance : RDS(on) typ = 80 m $\Omega$  (VGS = -4 V)
- Low drive voltage: 1.8 V drive
- Halogen-free / RoHS compliant

(EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

#### ■ Marking Symbol : MK

#### ■ Packaging

Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)



#### ■ Absolute Maximum Ratings Ta = 25 °C

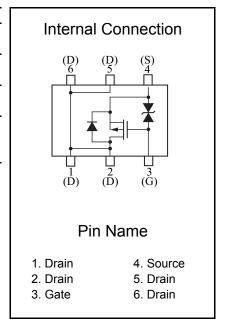
	Parameter	Symbol	Rating	Unit	
	Drain to Source Voltage	VDS	-20	V	
•	Gate to Source Voltage	VGS	±10	]	
-	Drain Current	ID	-2	Α	
	Drain Current (Pulsed) *1	IDp	-8		
	Total Power Dissipation	PD1 *2	540	mW	
		PD2 *3	150	11177	
	Channel Temperature	Tch	150		
	Operating Ambient Temperature	Topr	-40 to +85	°C	
	Storage Temperature Range	Tstg	-55 to +150		

- Note) \*1  $t \le 10 \mu s$ , Duty cycle  $\le 1 \%$ 
  - \*2 Glass epoxy substrate (25.4  $\times$  25.4  $\times$  t 0.8 mm) coated with copper foil (more than 300 mm $^2$ )
  - \*3 Non-heat sink

Established: 2008-01-09

Revised

: 2013-10-10



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#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VDS = 0 \text{ V}$			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = -1  mA, VDS = -10  V	-0.4	-0.75	-1.1	٧
Drain-source On-state Resistance *1	` ,	ID = -1 A, VGS = -4 V		80	120	mΩ
	RDS(on)2	ID = -1 A, VGS = -2.5 V		100	170	
	RDS(on)3	ID = -0.5 A, VGS = -1.8 V		140	230	
Forward transfer admittance *1	Yfs	ID = -1 A, $VDS = -10 V$ , $f = 1 kHz$	3			S
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V f = 1 MHz		300		pF
Output Capacitance	Coss			30		
Reverse Transfer Capacitance	Crss	1 = 1 1011 12		35		
Turn-on Delay Time *2	td(on)	VDD = -10 V, VGS = 0 to -4 V		6		ns
Rise Time *2	tr	ID = -1 A		8		
Turn-off Delay Time *2	td(off)	VDD = -10 V, VGS = -4 to 0 V		57		
Fall Time *2	tf	ID = -1 A		55		<u> </u>

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

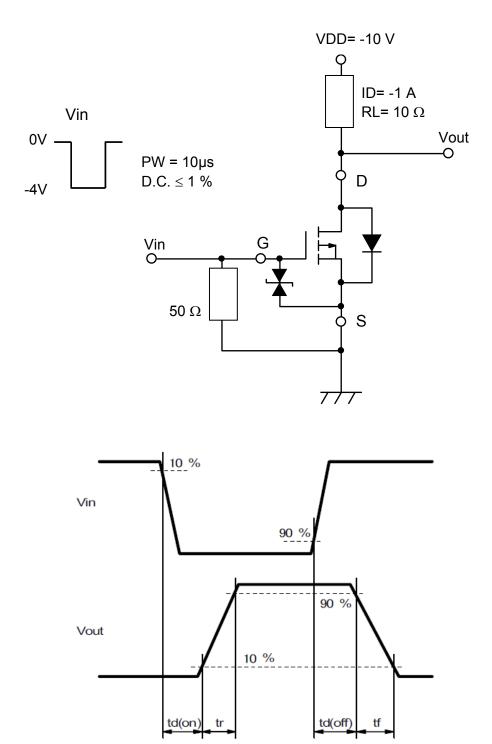
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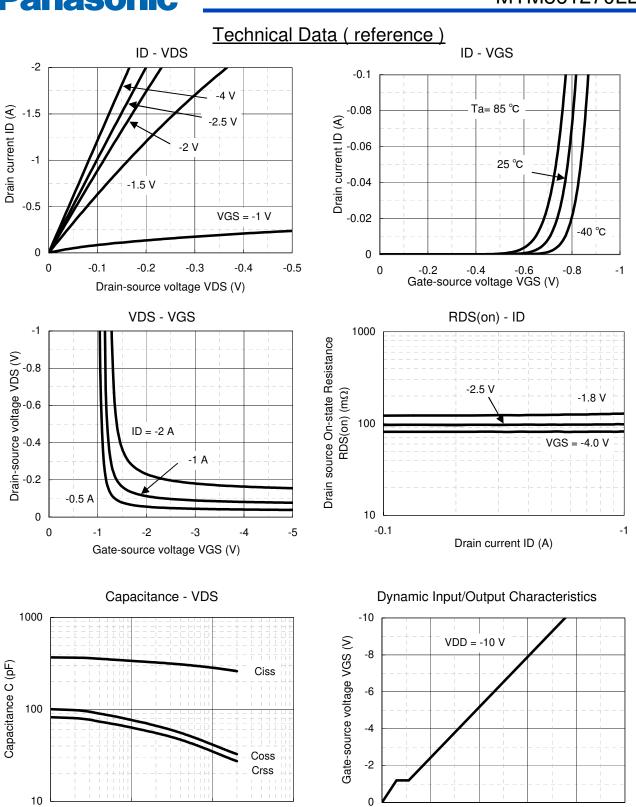
<sup>\*1</sup> Pulse test

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



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-0.1

-1

-10

Drain-source voltage VDS (V)

-100

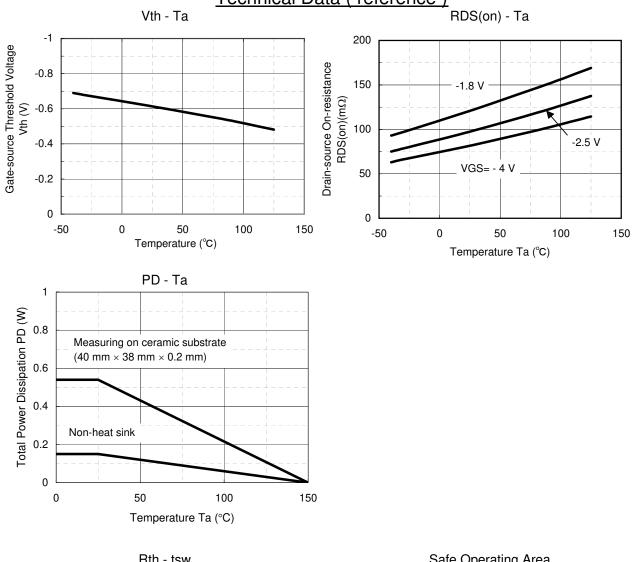
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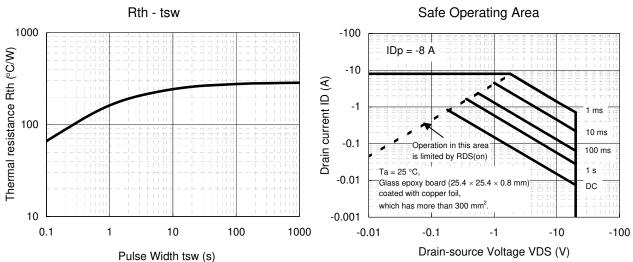
4

Total Gate Charge Qg (nC)

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# Technical Data (reference)



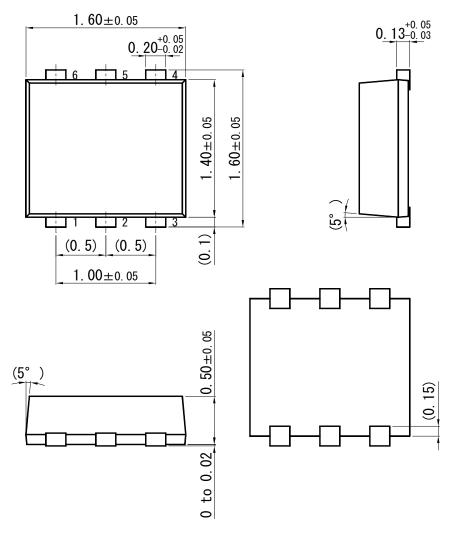


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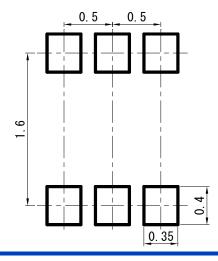
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WSSMini6-F1

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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